

# IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

PATENT APPLICATION

Inventors:

Wei Gao, and Yoshi Ono

Serial No:

10/677,006

Filed:

09/30/2003

Title:

MOSFET STRUCTURES WITH

CONDUCTIVE NBO GATES

Attorney Docket No. SLA0805

Group Art

2811

## **DECLARATION FOR PATENT APPLICATION**

As a below named inventor, I hereby declare that my residence, post office address and citizenship are as stated below next to my name; I believe that I am the original, first and sole inventor (if one name is listed below), or the first and joint inventor (if plural names are listed below), of the subject matter which is claimed and for which a patent is sought on the invention entitled,

## MOSFET STRUCTURES WITH CONDUCTIVE NBO GATES

the specification of which (check applicable ones):

is a	ttached	hereto;
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X was filed with the above-identified "Filed" date and assigned the above-identified "Serial No.";

was amended on (or amended through)
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I hereby state that I have reviewed and understand the contents of the above-identified specification, including the claims, as amended by any amendment(s) referred to above.

I acknowledge the duty to disclose information, which is material to the examination of the application in accordance with Title 37, Code of Federal Regulations, §1.56.

I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true, and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code and that such willful false statements may jeopardize the validity of the application or any patent issuing thereon.

Full name of sole or first inventor:  Residence:  2402 SE 180 <sup>th</sup> Ct Vancouver, WA 98607  Post Office Address:  Same  Citizenship:  People's Republic of China  Inventor's signature:  Date:  1/21/2004  Full name of second inventor:  Yoshi Ono  Residence:  2526 NW 24th Circle Camas, WA 98607  Post Office Address:  Same  Citizenship:  USA  USA  USA/2004		
Vancouver, WA 98607  Post Office Address: Same  Citizenship: People's Republic of China  Inventor's signature:  Date: I/21/200#  Full name of second inventor: Yoshi Ono  Residence: 2526 NW 24th Circle Camas, WA 98607  Post Office Address: Same  Citizenship: USAMA  Inventor's signature:		Wei Gao
Citizenship: People's Republic of China  Inventor's signature:  Date: I/21/2004  Full name of second inventor: Yoshi Ono  Residence: 2526 NW 24th Circle Camas, WA 98607  Post Office Address: Same  Citizenship: USA  Inventor's signature:	Residence:	
Inventor's signature:  Date:  I / 21 / 200 /   Full name of second inventor:  Yoshi Ono  Residence:  2526 NW 24th Circle Camas, WA 98607  Post Office Address:  Citizenship:  USA  USA  USA  USA  USA  USA  USA  US	Post Office Address:	Same
Date:	Citizenship:	People's Republic of China
Full name of second inventor:  Yoshi Ono  Residence:  2526 NW 24th Circle Camas, WA 98607  Post Office Address:  Same  Citizenship:  USA  USA  USA  USA  USA	Inventor's signature:	J. CR.
Residence:  Camas, WA 98607  Post Office Address:  Same  Citizenship:  USA  UNA  UNA  UNA  UNA  UNA  UNA  UNA	Date:	1/21/2004
Residence:  Camas, WA 98607  Post Office Address:  Same  Citizenship:  USA  UNA  UNA  UNA  UNA  UNA  UNA  UNA	* * * * * * * * * * * * * * * * * * *	****************
Camas, WA 98607  Post Office Address: Same  Citizenship: USA  Inventor's signature:		Yoshi Ono
Citizenship: USA Description of the Control of the	Residence:	
Inventor's signature:	Post Office Address:	Same
1/21/2004	Citizenship:	USA
Date:	Inventor's signature:	Chiefe -
	Date:	1/21/2004



## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

PATENT APPLICATION

Inventors:

Wei Gao, and Yoshi Ono

Serial No:

Not Yet Assigned

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Title:

MOSFET STRUCTURES WITH

CONDUCTIVE NBO GATES

Attorney Docket No. SLA0805

#### **DECLARATION FOR PATENT APPLICATION**

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## MOSFET STRUCTURES WITH CONDUCTIVE NBO GATES

the specification of which (check applicable ones):

- X is attached hereto;
- \_ was filed with the above-identified "Filed" date and assigned the above-identified "Serial No.";
- \_ was amended on (or amended through) \_\_\_\_.

I hereby state that I have reviewed and understand the contents of the aboveidentified specification, including the claims, as amended by any amendment(s) referred to above.

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Full name of sole or first inventor:	Wei Gao
Residence:	2402 SE 180 <sup>th</sup> Ct Vancouver, WA 98607
Post Office Address:	Same
Citizenship:	People's Republic of China
Inventor's signature:	
Date: <u>9/30/</u>	200 <u>3</u> ****************************
Full name of second inventor:	Yoshi Ono
Residence:	2526 NW 24th Circle Camas, WA 98607
Post Office Address:	Same
Citizenship:	USA
Inventor's signature:	AND ES
Date:	9/30/03

## **ASSIGNMENT**

WHEREAS, the undersigned Wei Gao, a resident of Vancouver, WA; and Yoshi Ono, a resident of Camas, WA, (hereinafter termed "Inventors") have invented certain new and useful improvements in:

#### MOSFET STRUCTURES WITH CONDUCTIVE NBO GATES

and have executed a declaration or oath for an application for a United States patent disclosing and identifying the invention:

X	Declaration executed on September 30, 2003;
	or
	Having been previously filed and assigned Serial Number and filing date; and

WHEREAS Sharp Laboratories of America, Inc., a corporation of the State of Washington, (hereinafter termed "Assignee"), having a place of business at 5750 NW Pacific Rim Boulevard, Camas, State of Washington, wishes to acquire the entire right, title and interest in and to said application and the invention disclosed therein, and in and to all embodiments of the invention, heretofore conceived, made or discovered by said Inventors (all collectively hereinafter termed "said invention"), and in and to any and all patents, certificates of invention and other forms of protection thereon (hereinafter termed "patents") applied for or granted in the United States and/or other countries.

NOW THEREFORE, for good and valuable consideration acknowledged by said Inventors to have been received in full from said Assignee:

1. Said Inventors hereby sell, assign, transfer and convey unto said Assignee, the entire right, title and interest (a) in and to said application and said invention; (b) in and to all rights to apply in any and all countries of the world for patents, certificates of inventions or other government grants on said invention, including the right to apply for patents pursuant to the International Convention for the Protection of Industrial property or pursuant to any other convention, treaty, agreement or understanding; (c)

in and to any and all applications filed and any and all patents, certificates of inventions or other governmental grants granted on said invention in the United States or any other country, including each and every application filed and each and every patent granted on any application which is a division, substitution, or continuation of any of said applications; (d) in and to each and every reissue or extension of any of said patents; and (e) in and to each and every patent claim resulting from a reexamination certificate for any and all of said patents.

- 2. Said Inventors hereby covenant and agree to cooperate with said Assignee to enable said Assignee to enjoy to the fullest extent the right. title and interest herein conveyed in the United States and other countries. Such cooperation by said Inventors shall include prompt production of pertinent facts and documents, giving of testimony, executing of petitions, oaths, specifications, declarations or other papers, and other assistance all to the extent deemed necessary or desirable by said Assignee (a) for perfecting in said Assignee the right, title and interest herein conveyed; (b) for complying with any duty of disclosure; (c) for prosecuting any of said applications; (d) for filing and prosecuting substitute, divisional, continuing or additional applications covering said invention; (e) for filing and prosecuting application for reissue of any of said patents; (f) for interference or other priority proceedings involving said invention; and (g) for legal proceedings involving said invention and any applications therefore and any patents granted thereon, including without limitation opposition proceedings, cancellation proceedings, priority contests, public use proceedings, reexamination proceedings, compulsory licensing proceedings, infringement actions and court actions; provided, however, that the expense incurred by said Inventors in providing such cooperation shall be paid for by said Assignee.
- 3. The terms and covenants of this Assignment shall inure to the benefit of said Assignee, its successors, assigns and other legal representatives, and shall be binding upon said Inventors, said Inventors' heirs, legal representatives and assigns.
- 4. Said Inventors hereby warrant and represent that said Inventors have not entered and will not enter into any assignment, contract, or understanding in conflict with this assignment.

IN WITNESS WHEREOF, the said Inventors have executed this Assignment on the date given below:

(1) Wei Gao (Signature)	$\frac{9/30/03}{\text{(Date)}}$
****************	******************************
(2) Yoshi Ono (Signature)	<u>9/30/03</u> (Date)